

isc N-Channel MOSFET Transistor

BUZ76A

DESCRIPTION

- 2.6A, 400V
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

APPLICATIONS

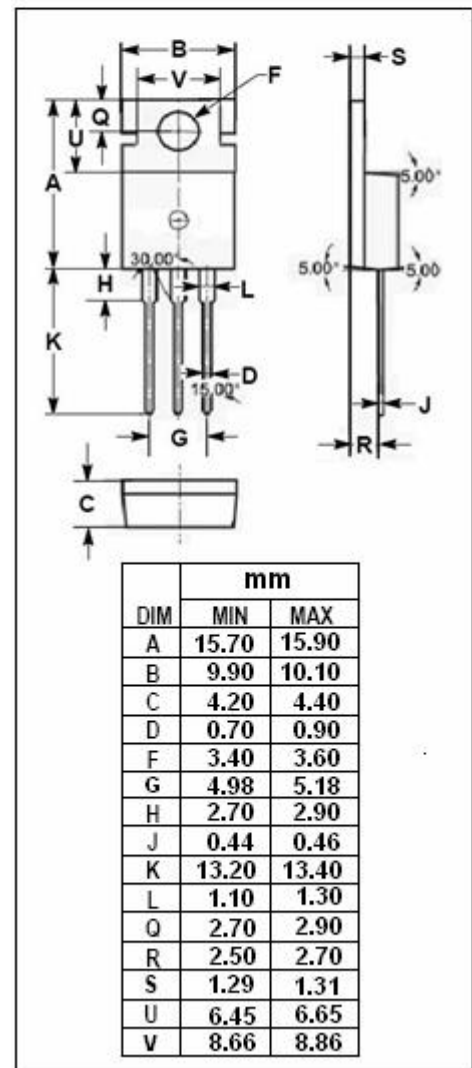
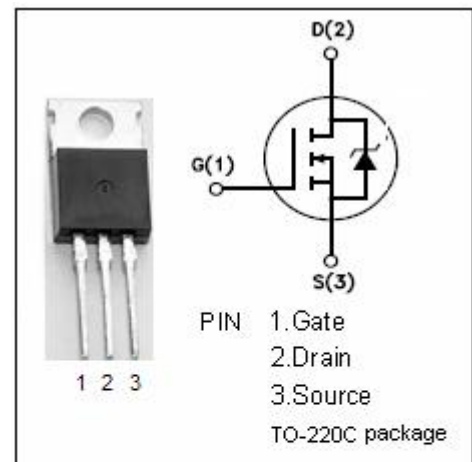
• applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power.

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	400	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	2.6	A
P _{tot}	Total Dissipation@TC=25°C	40	W
T _j	Max. Operating Junction Temperature	-55-150	°C
T _{stg}	Storage Temperature Range	-55-150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	3.1	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	75	°C/W



isc N-Channel Mosfet Transistor**BUZ76A****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	400		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.1	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 1.5A		2.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400V; V _{GS} = 0		250	uA
V _{SD}	Diode Forward Voltage	I _F = 5.2A; V _{GS} = 0		1.4	V